

ABSTRACT

A rectangular parallelepiped projecting portion 21 having a height of H_B and a width of W_B is formed on a silicon substrate, and a gate oxide film is formed on a part of the top surface and the side surface of the projecting portion 21. A source and a drain are formed on both sides of the gate electrode 26 to form a MOS transistor. The MOS transistor configures a DC amplifier. The DC amplifier includes a differential amplification circuit having MOS transistors 61 and 62, thereby realizing a high-gain DC amplifier.